

The background features a collage of images related to circuit simulation. At the top center, there is a schematic diagram of a circuit board with various components and connections. Below it, a large white rounded rectangle contains the title and authors. In the bottom left, there is a 3D wireframe model of a circuit board layout. In the bottom center, there is a 3D visualization of a circuit board with a color-coded simulation result, showing a gradient from blue to red. In the bottom right, there is a 3D visualization of a circuit board with a blue and white simulation result. The ANSOFT logo is located in the bottom right corner of the white rectangle.

Recent Advancements in Circuit Simulation Technology

By

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Michael Tsuk

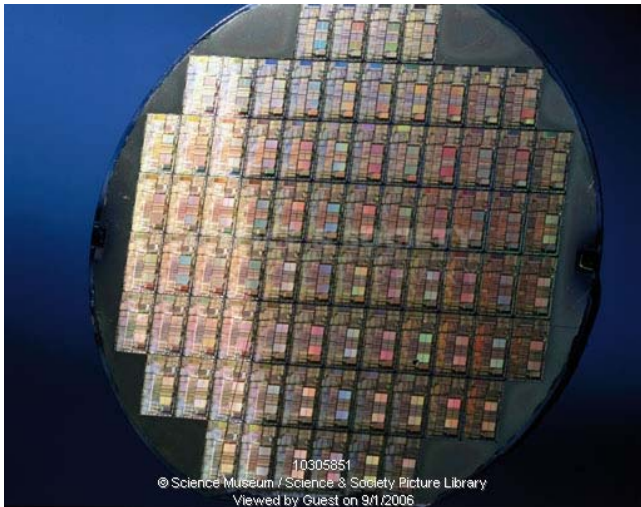
Mary Tolikas

Mark Reichelt



Circuit simulation that supports emerging electronic design trends

Trend: Nanometer-device geometries



Large simulation **capacity** to handle:

- Substrate coupling effects
- High level of integration

Circuit simulation that supports emerging electronic design trends

Trend: Bridging the gap between system to component design

Simulation ***flexibility*** to handle:

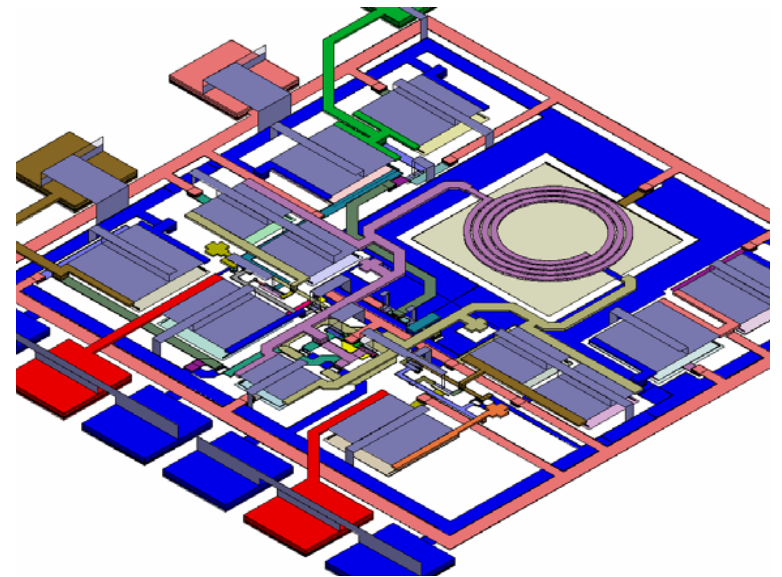
- Models from different vendors and description languages (Verilog, Spice, IBIS, TSTONE,...)
- Varying levels of model abstraction (physical, *circuit to behavioral*)

Circuit simulation that supports emerging electronic design trends

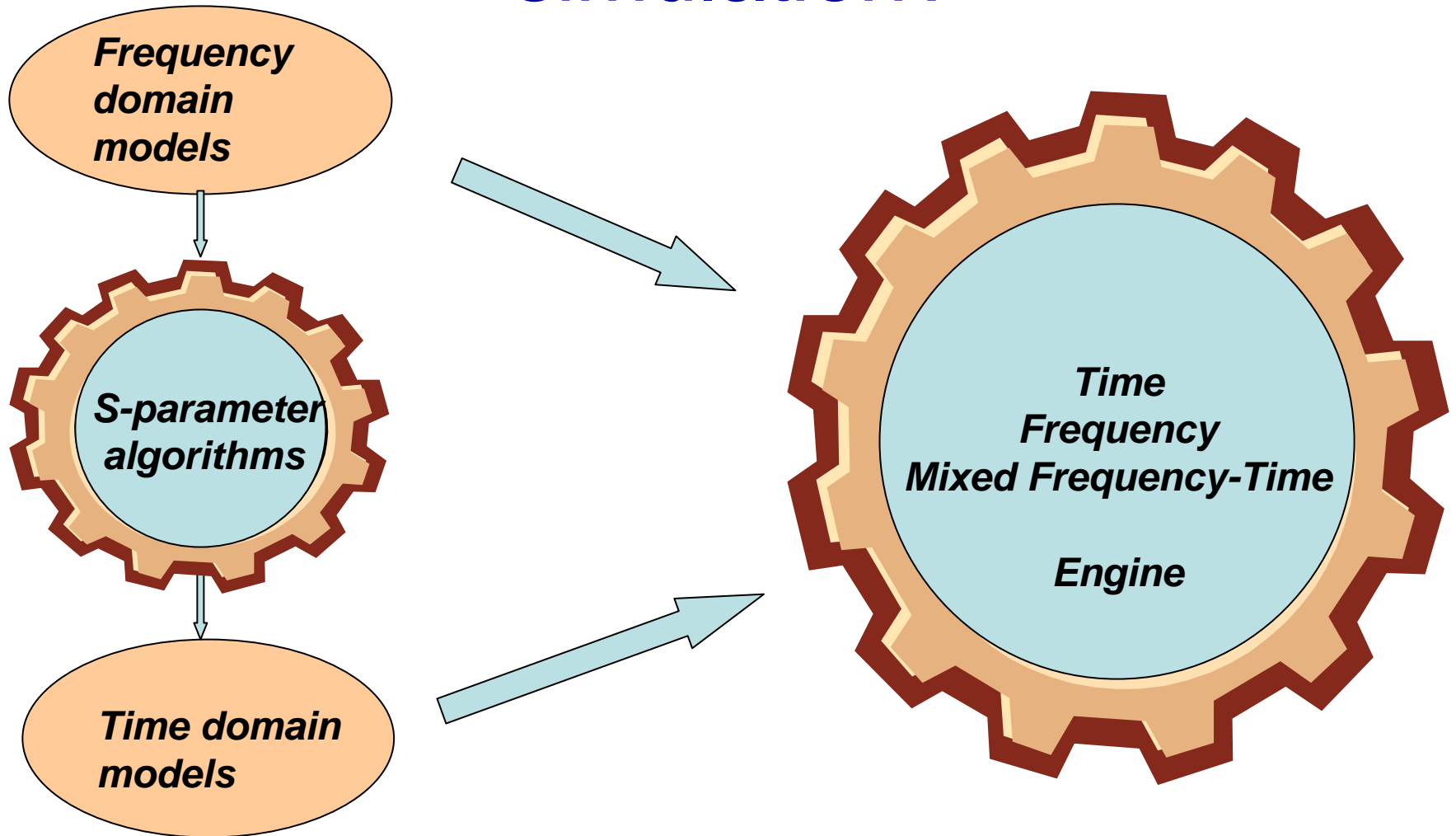
Trend: Identify and locate sources of unwanted coupling

Simulation ***link to EM*** to handle:

- Insight provided by EM simulators on the physical structures



What does this mean for circuit simulation?



Simple linear system at the core

Formulating equations from schematics

Matrix of conservation laws
& constitutive equations

Sources

$$Ax = b$$

Vector of unknown node voltages
& branch currents

Simple linear system at the core

$$Ax = b$$

Even larger circuits
Ever more couplings
& nonlinearities

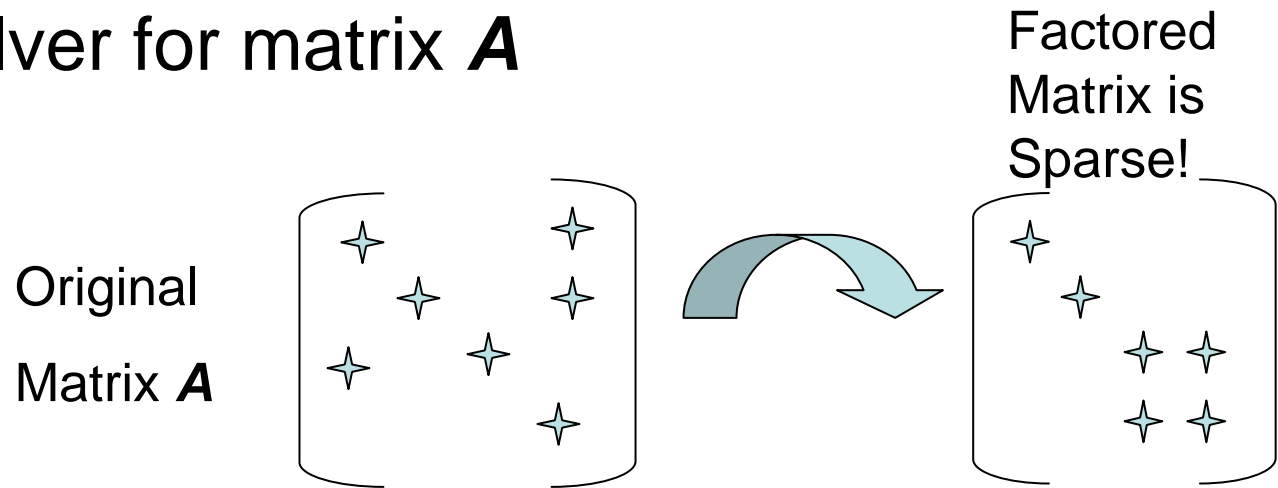


A (and x) increase in size!
A less sparse

“Invert” huge matrix as fast as possible to obtain x!

Simulation speed depends on sparsity of A

- Sparse solver for matrix A



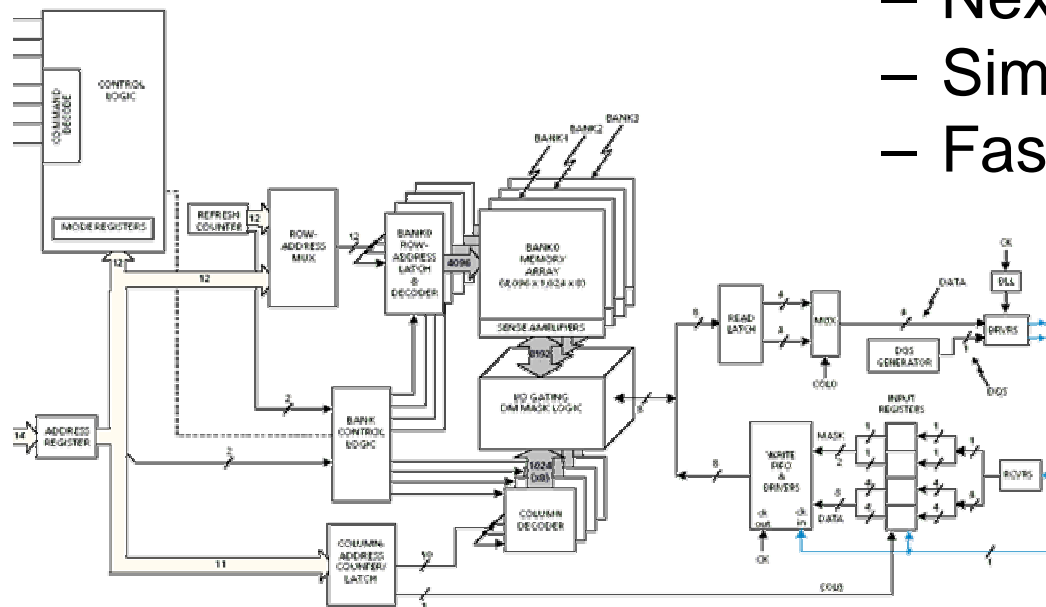
– Nexxim's efficiency stems from:

- Smart application of a number of Graph-Based Sparse Matrix Algorithms
- Particularly important in transient analysis

Direct sparse solution for large circuits

- Transient Simulation on digital AND analog section of DDR SDRAM

- Nexxim: 3 hours
- SimulatorB: 12 hours
- Fast Spice: Wrong results



Other analyses require iterative solvers & preconditioners

- Iterative solver for matrix **A**
 - Looks for x in the space

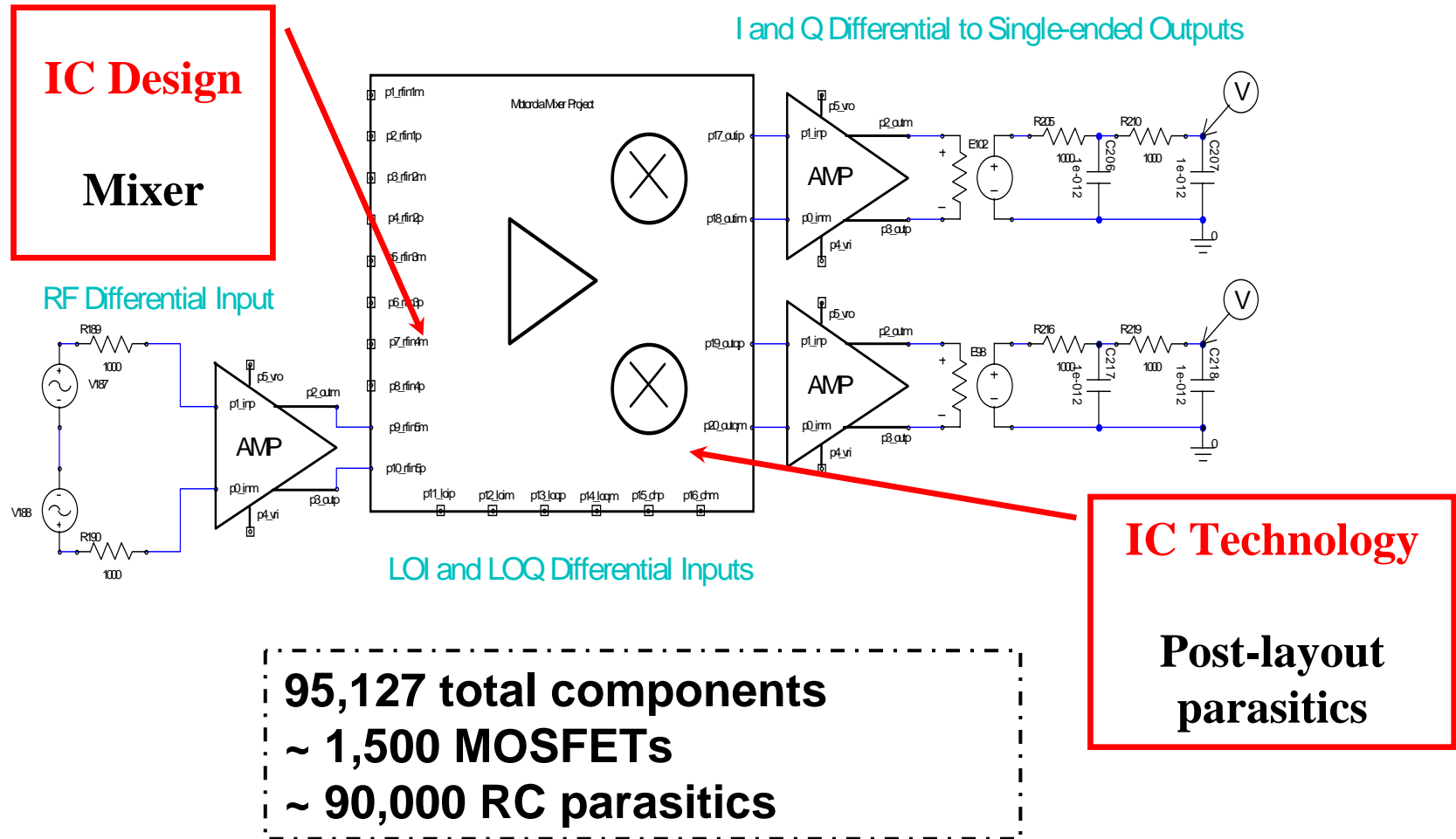
$x \in \{b, Ab, A^2b, \dots, A^{k-1}b\}$ where $k \ll \text{size}(A)$

- Nexxim uses “Preconditioner” **P** that makes **k** as small as possible

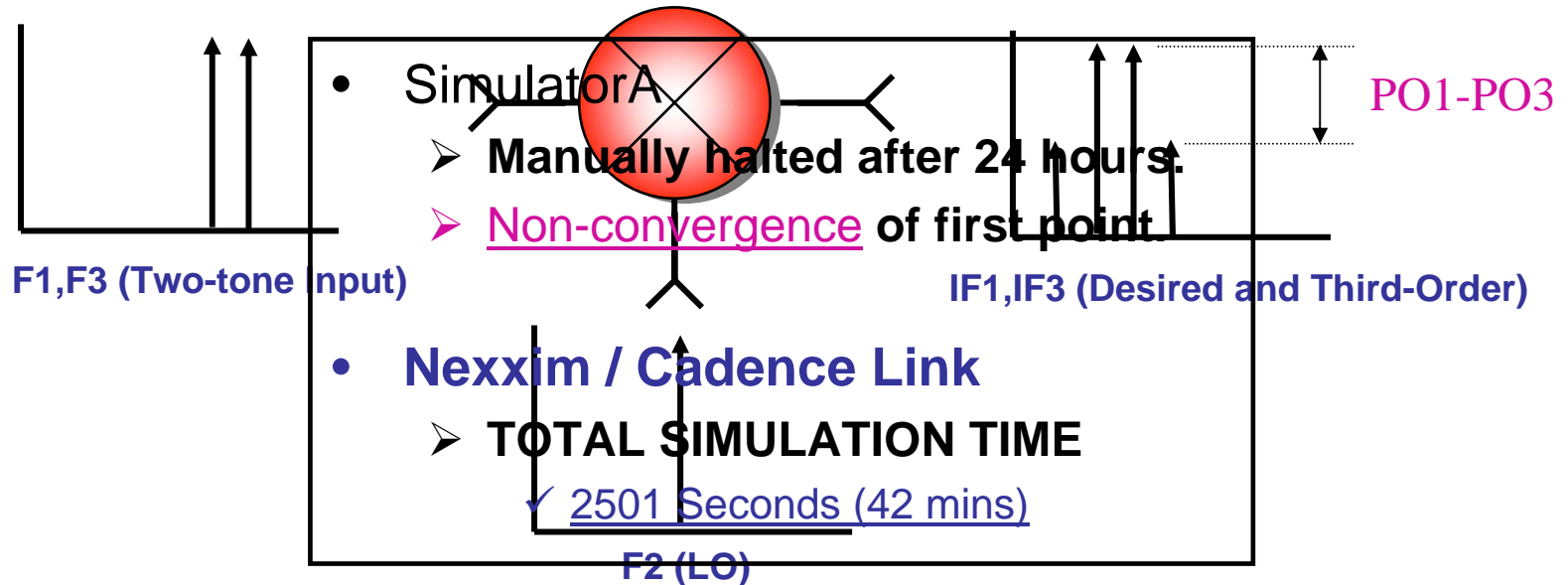
$$PAx = Pb$$

- Nexxim’s Efficiency from choice of **P** and a family of Iterative Solvers

Iterative solution for large circuits



Smart preconditioning enables fast linearity simulations



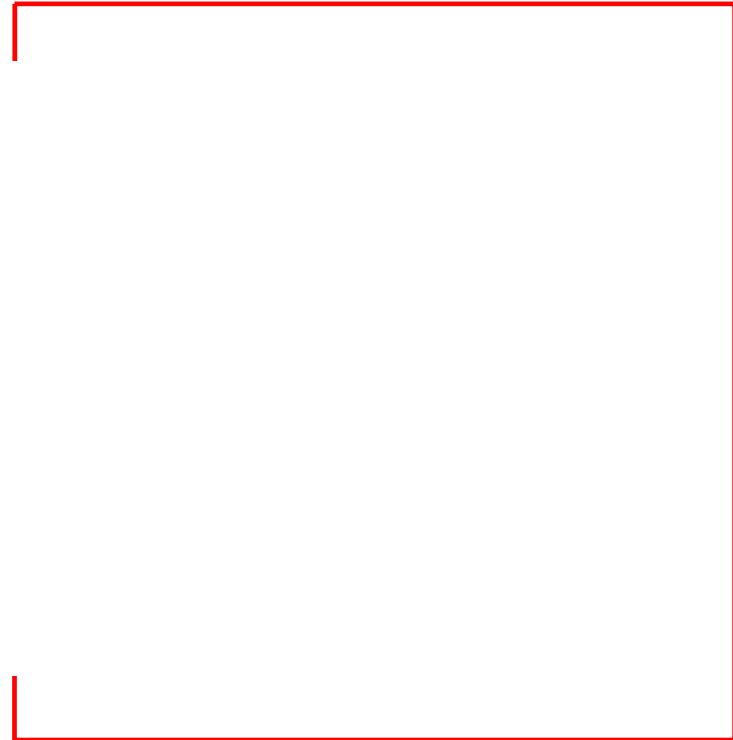
3-Tone Harmonic Balance [F1, F2, F3]

- F1 = 1.07GHz (RF #1) with 2 Harmonics
- F2 = 1.00GHz (LO) with 1 Harmonic
- F3 = 1.06GHz (RF #2) with 2 Harmonics
- Input Power : 5 points sweep

Efficient algorithms for accuracy

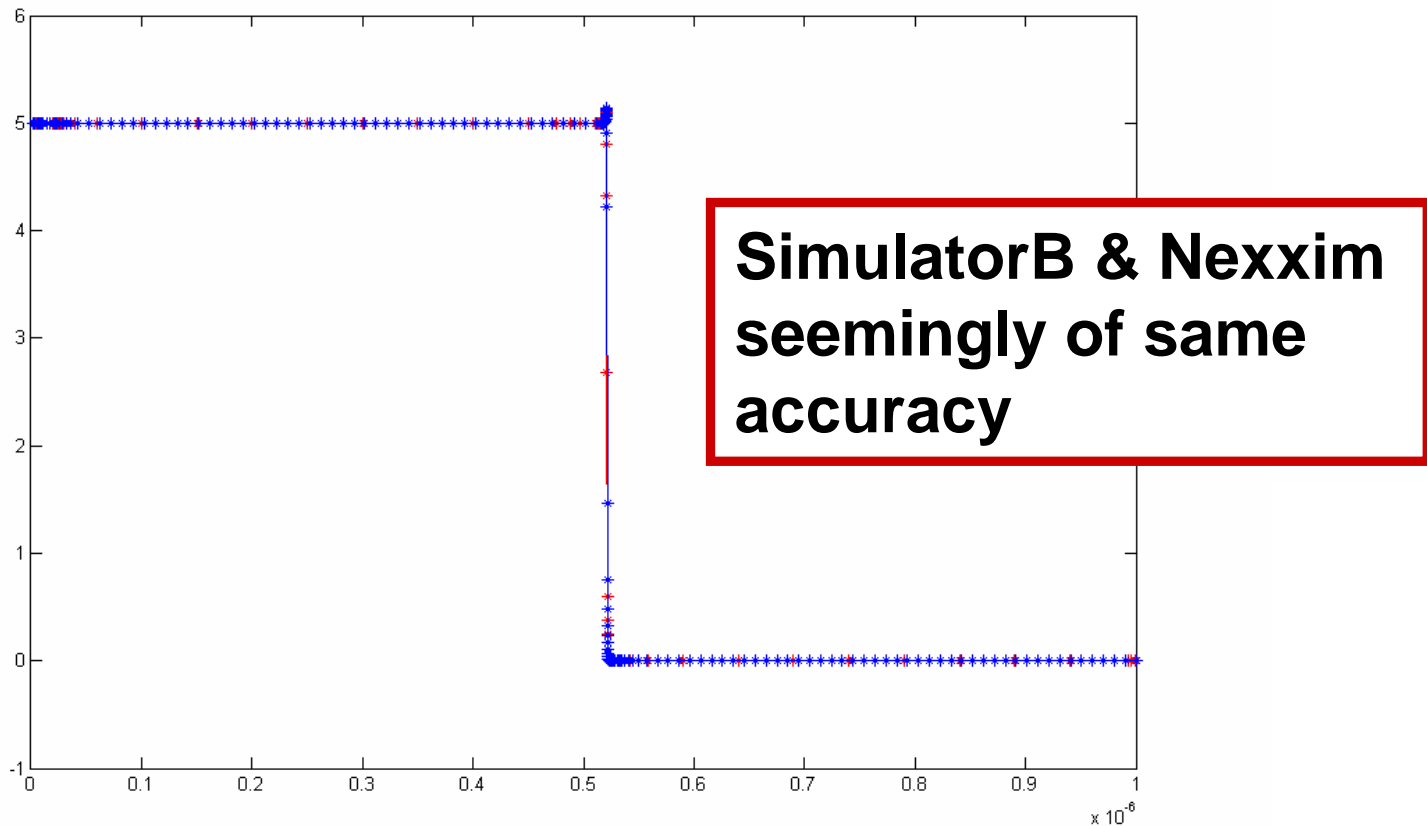
- Choose Time points With Efficient Error Control Algorithm

Transient analysis:

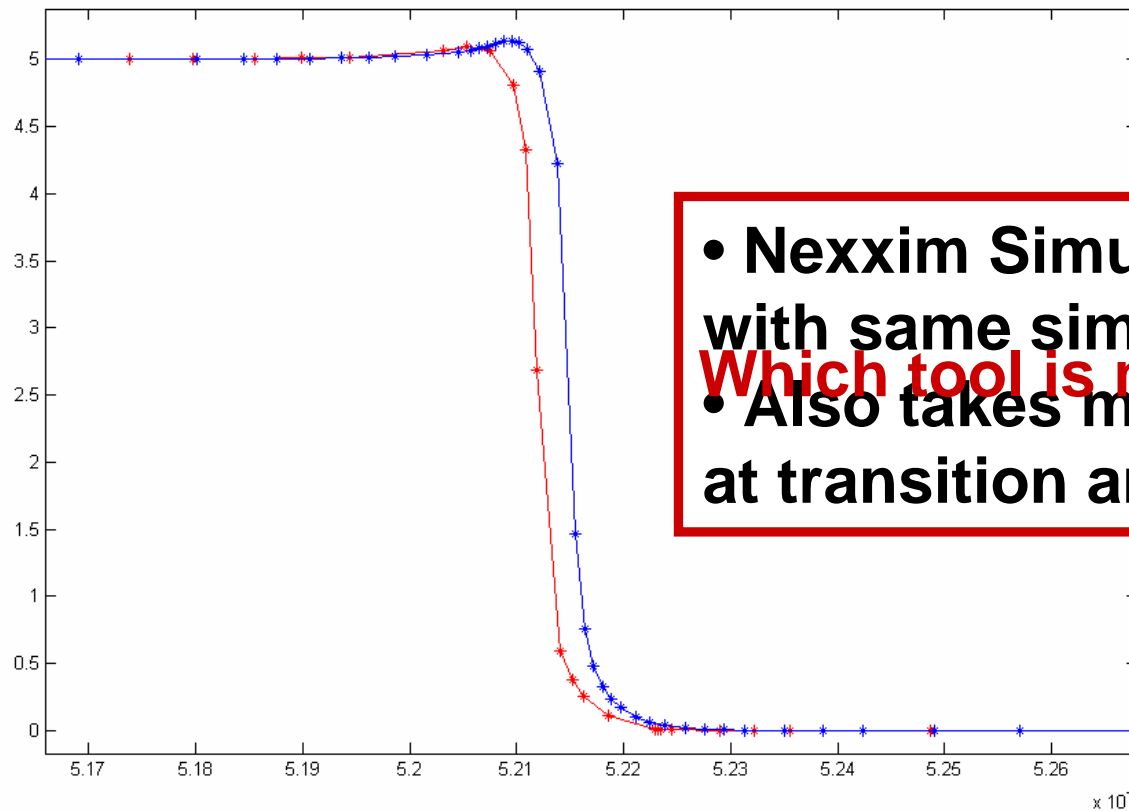


Efficient algorithms for accuracy

- CMOS inverter chain

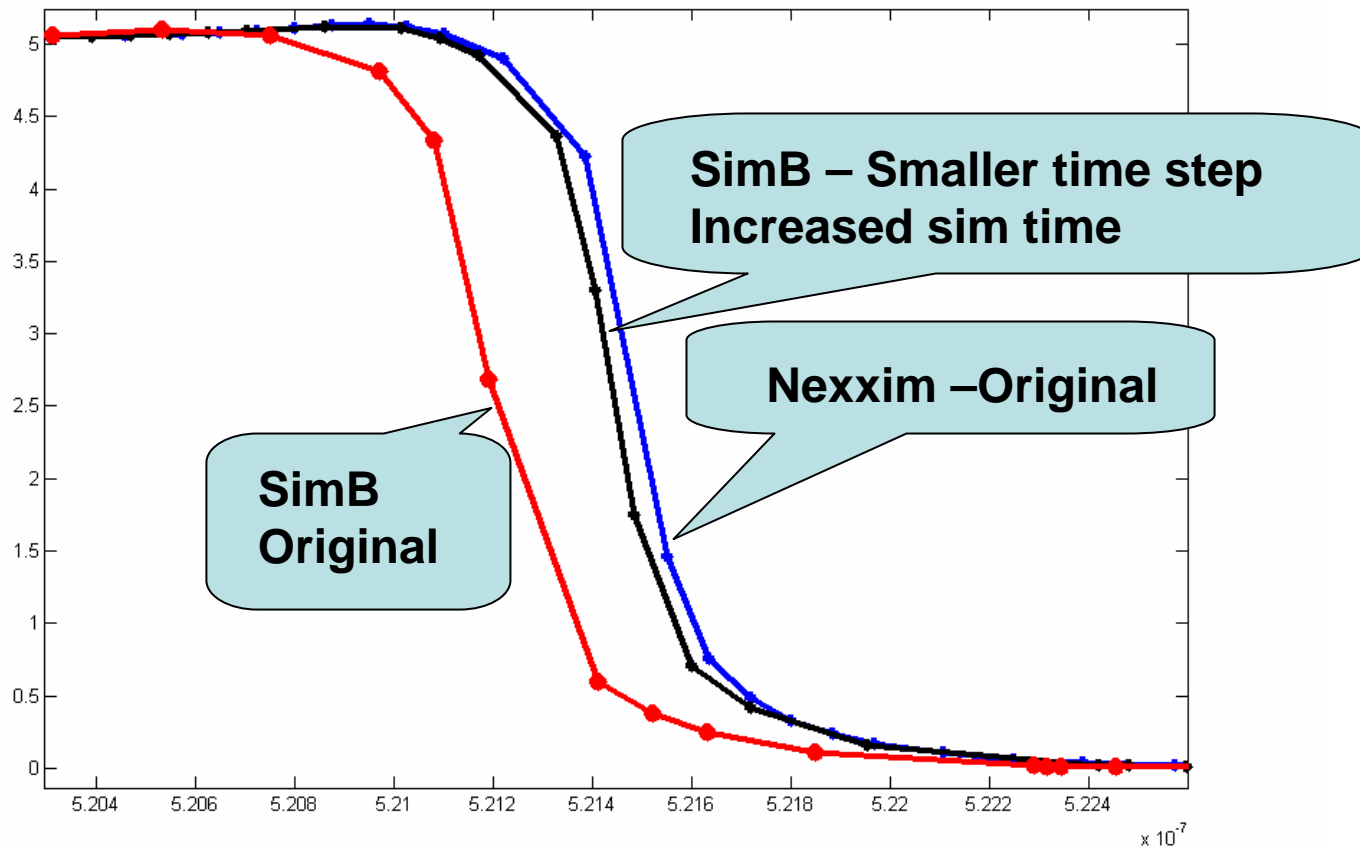


Efficient algorithms for accuracy



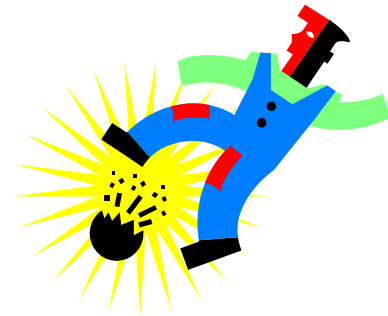
- Nexxim Simulation speed faster with same simulation tolerances
 - Also takes more time points at transition areas
- Which tool is more accurate?**

Efficient algorithms for accuracy



Ensuring accuracy across simulation domains

- S-parameters
 - Fundamental issue: S-parameters in frequency domain, simulation in time domain.
 - On surface, simple: inverse FFT, impulse response, convolution



Ensuring accuracy across simulation domains

Transient Simulation of S-parameters *Causality and passivity*

- For causality, effects follow causes
 - Impulse responses must be 0 for $t < 0$
- For passivity, does the S-parameter block generate or absorb power?
 - At each frequency, the maximum singular value (SVD) of the S matrix ≤ 1

Ensuring accuracy across simulation domains

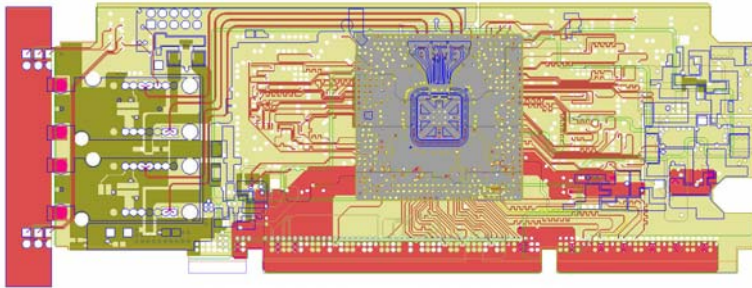
- Traditional method of ***Convolution***
 - Can be slow (numerical integration)
 - Limited frequency of data
 - Windowing effects in iFFT
 - If data not on uniform grid, Interpolation, not necessarily causal or passive
 - Need care to avoid filtering effects

Ensuring accuracy across simulation domains

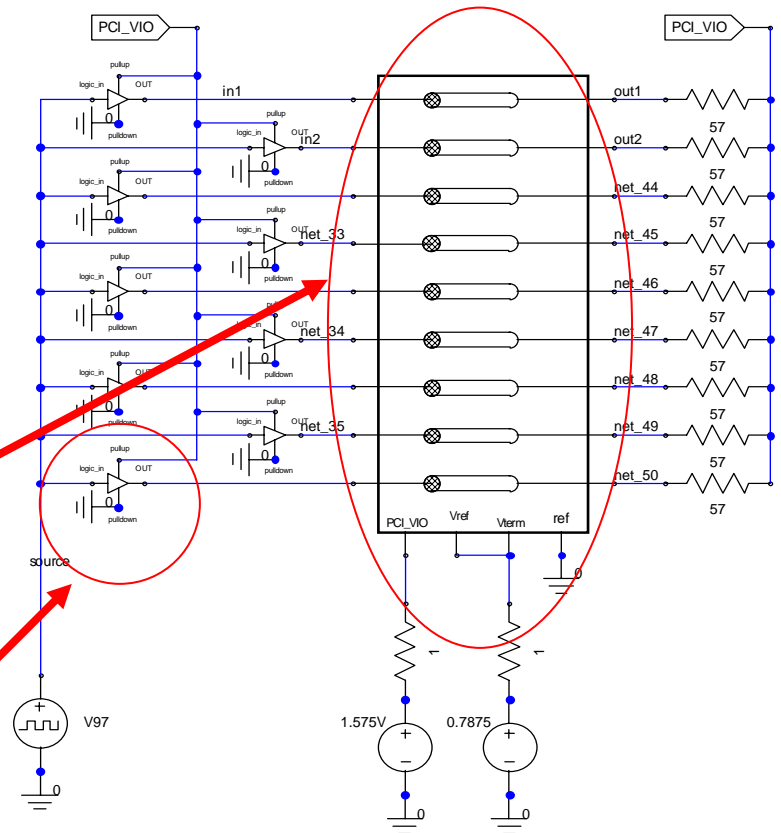
- Nexxim's preferred approach is ***State Space***
 - Pole-residue fit to frequency-domain data
 - Only stable poles used: causal
 - Very efficient transient simulation
 - Simple first-order differential equation
 - Passivity not guaranteed
 - But can be enforced for moderate-sized problems

Board design example

Simultaneous Switching and Power Integrity



**57 Port S-parameter block
DC to 5GHz**



IBIS Drivers

Board design

Solving the circuit with state-space

57 Port S-parameter block used to generate state-space model

In frequency domain: $Y(s) = H(s) U(s)$

In time domain (state space model):

$$\dot{x}(t) = Ax(t) + Bu(t)$$

$$y(t) = Cx(t) + Du(t)$$

using the equivalence:

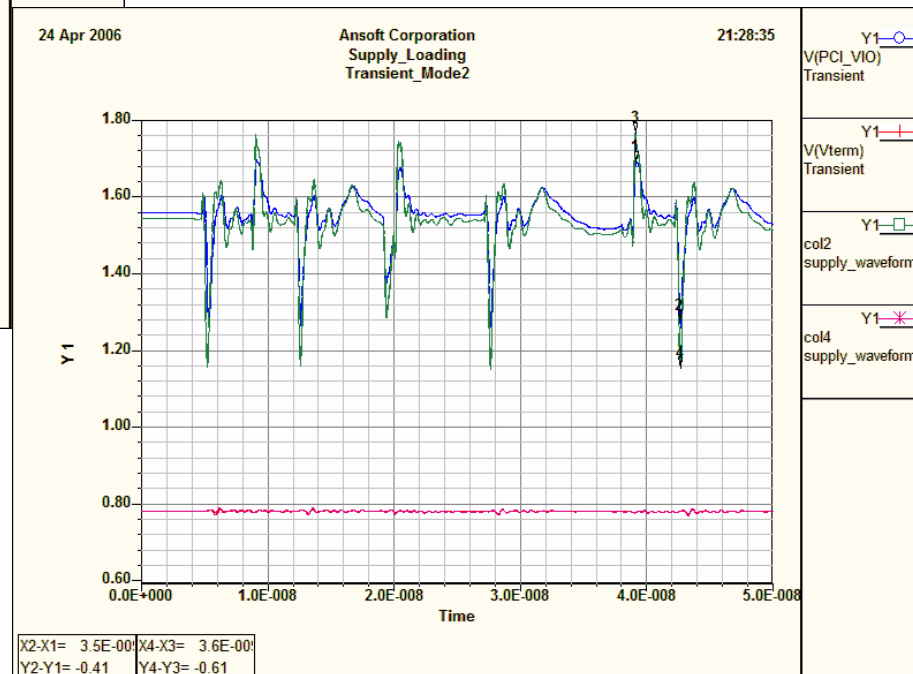
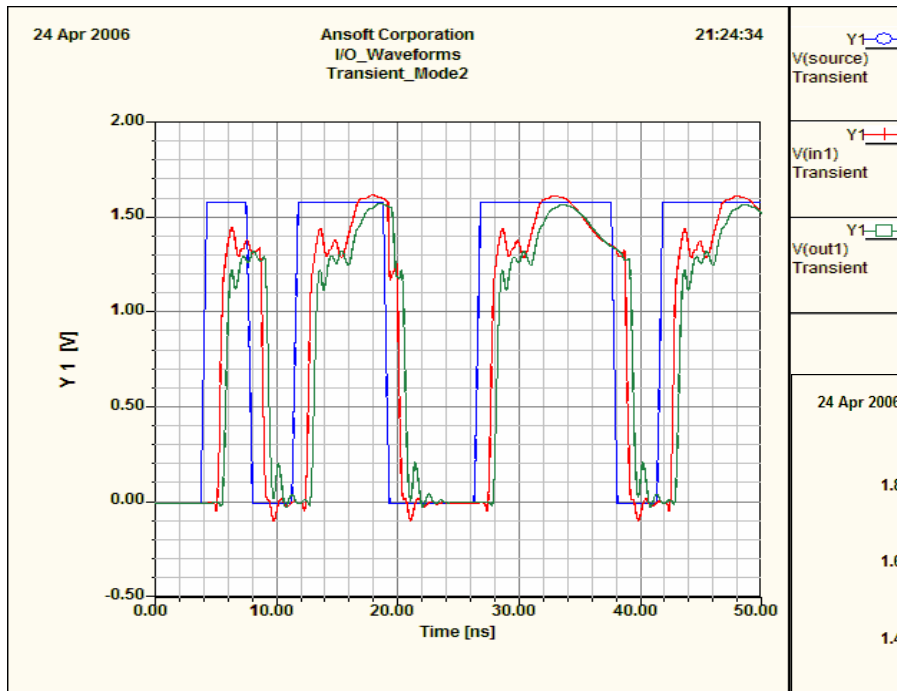
$$H(s) = C(sI - A)^{-1}B + D$$

Transient analysis results using Nexxim

18 IBIS Drivers

57 Port S-parameter model

Transient simulation time: 366s



Taking advantage of state-space caching

Improvements to Nexxim's handling of S-parameters, including model-order reduction and passivity enforcement of the state-space formulation take computation time; in the case of passivity enforcement, a lot of time!



Run simulation for the 1st time



State-space fitting



Generation of a .sss file with the state space model details

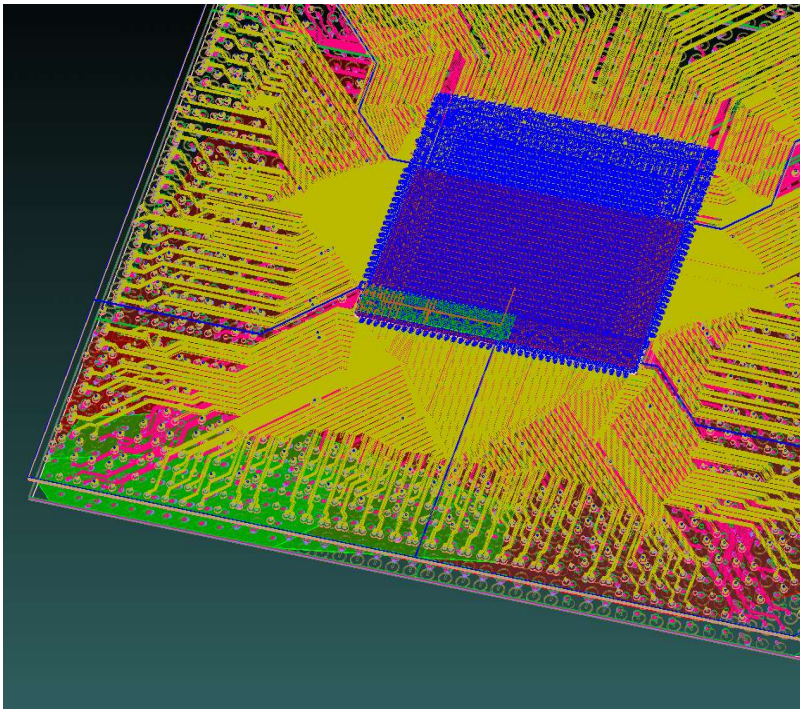


Used in subsequent runs with unchanging S-parameter data



**Save simulation time!
No need to regenerate
the state space model**

Pushing the envelope in capacity, speed and accuracy



SIwave Package Model

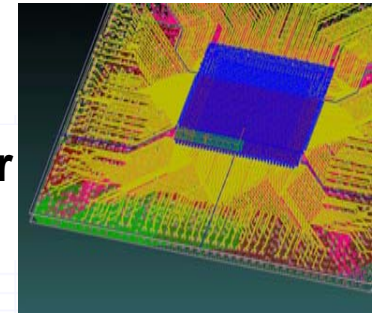
44-port S-parameter model

Frequency range of 0-10GHz

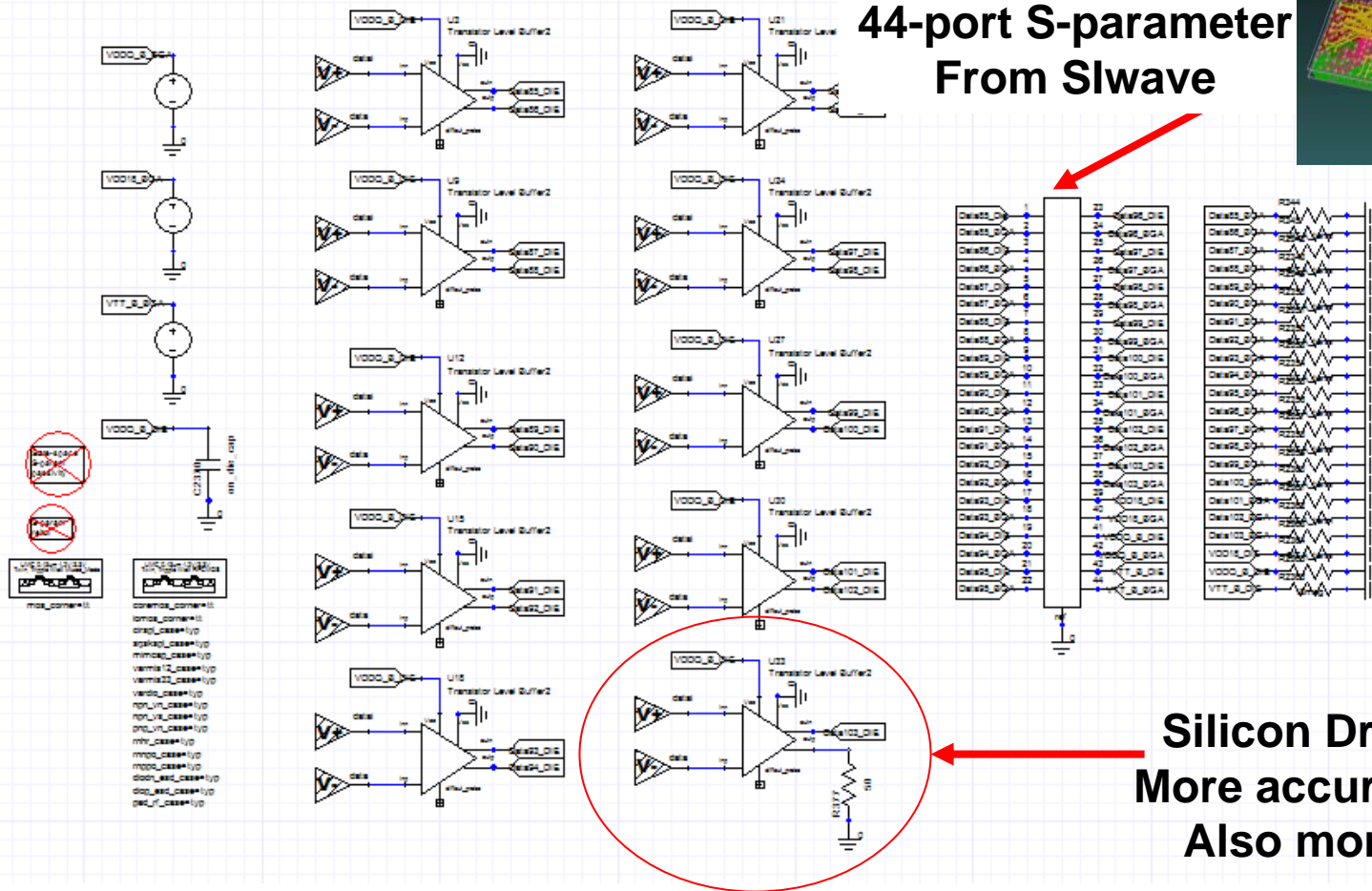
Model includes both power structures and signal nets

Chip and Package Design

Setting up the circuit simulation in DesignerSI



44-port S-parameter From Slwave

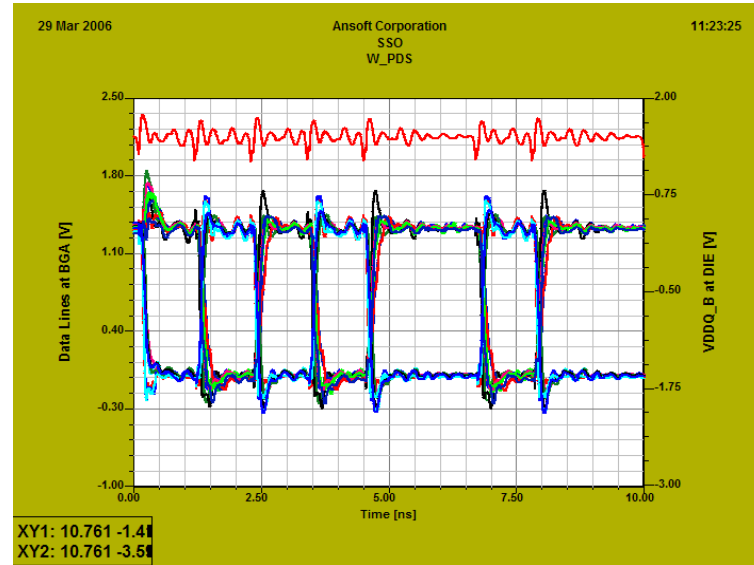
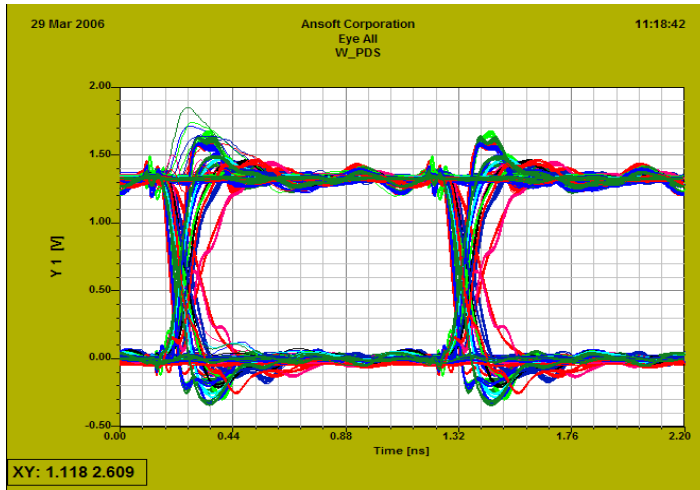


**Silicon Driver Models
More accurate than IBIS
Also more complex**

Chip and Package Design

64-bit Nexxim

44 port S-parameter model
148,000 MOSFETs
1.7 Million Capacitors
500,000 Resistors



Nexxim solution time: 36 hrs

Conclusion

Capacity, Speed, Accuracy

for increasingly large and complex circuits